MMBT4401M3T5G

NPN Switching Transistor

The MMBT4401M3T5G device is a spin−off of our popular SOT−23 three−leaded device. It is designed for general purpose switching applications and is housed in the SOT−723 surface mount package. This device is ideal for low−power surface mount applications where board space is at a premium.

Features

- Reduces Board Space
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	40	Vdc
Collector−Base Voltage	V_{CBO}	60	Vdc
Emitter−Base Voltage	V_{EBO}	6.0	Vdc
Collector Current − Continuous	I_C	600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board (Note 1) $T_A = 25°C$ Derate above 25°C	P_D	265 2.1	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	470	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25°C$ Derate above 25°C	P_D	640 5.1	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	195	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.
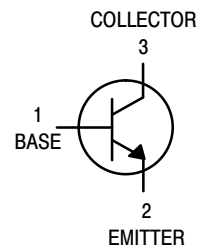1. FR−5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.

ON Semiconductor®

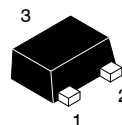COLLECTOR
3

1
BASE

2
EMITTER

MARKING DIAGRAM

SOT−723
CASE 631AA
STYLE 1

AF M

AF = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping[†]
MMBT4401M3T5G	SOT−723 (Pb−Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 3)	(I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	–	Vdc
Collector – Base Breakdown Voltage	(I_C = 0.1 mAdc, I_E = 0)	$V_{(BR)CBO}$	60	–	Vdc
Emitter – Base Breakdown Voltage	(I_E = 0.1 mAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	–	Vdc
Base Cutoff Current	(V_{CE} = 35 Vdc, V_{EB} = 0.4 Vdc)	I_{BEV}	–	0.1	μAdc
Collector Cutoff Current	(V_{CE} = 35 Vdc, V_{EB} = 0.4 Vdc)	I_{CEX}	–	0.1	μAdc
ON CHARACTERISTICS (Note 3)					
DC Current Gain		h_{FE}			–
	(I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc)		20	–	
	(I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc)		40	–	
	(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)		80	–	
	(I_C = 150 mAdc, V_{CE} = 1.0 Vdc)		100	300	
	(I_C = 500 mAdc, V_{CE} = 2.0 Vdc)		40	–	
Collector – Emitter Saturation Voltage		$V_{CE(sat)}$			Vdc
	(I_C = 150 mAdc, I_B = 15 mAdc)		–	0.4	
	(I_C = 500 mAdc, I_B = 50 mAdc)		–	0.75	
Base – Emitter Saturation Voltage		$V_{BE(sat)}$			Vdc
	(I_C = 150 mAdc, I_B = 15 mAdc)		0.75	0.95	
	(I_C = 500 mAdc, I_B = 50 mAdc)		–	1.2	
SMALL–SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product	(I_C = 20 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	250	–	MHz
Collector–Base Capacitance	(V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	C_{cb}	–	6.5	pF
Emitter–Base Capacitance	(V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{eb}	–	30	pF
Input Impedance	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{ie}	1.0	15	kΩ
Voltage Feedback Ratio	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{re}	0.1	8.0	X 10^{-4}
Small – Signal Current Gain	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{fe}	40	500	–
Output Admittance	(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{oe}	1.0	30	μmhos
SWITCHING CHARACTERISTICS					
Delay Time	(V_{CC} = 30 Vdc, V_{EB} = 2.0 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_d	–	15	ns
Rise Time		t_r	–	20	
Storage Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_s	–	225	ns
Fall Time		t_f	–	30	

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUITS
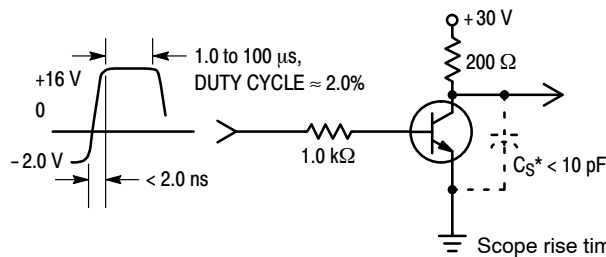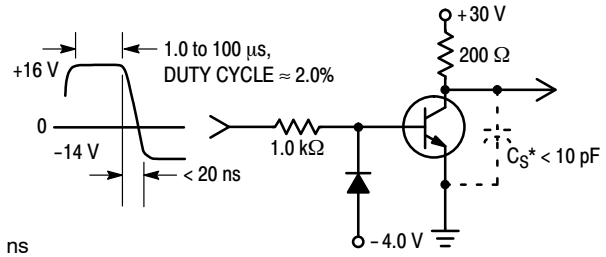

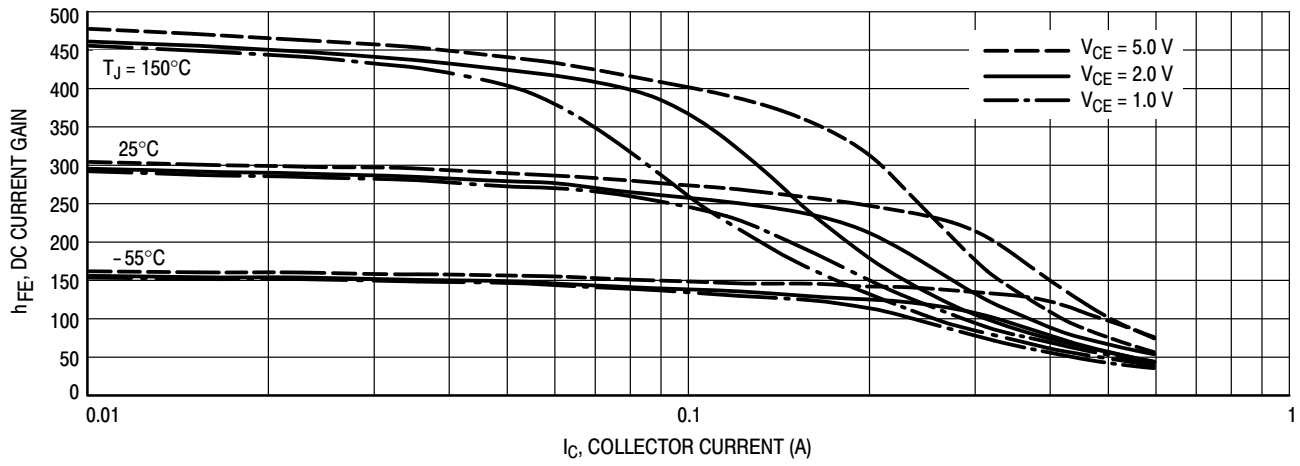Figure 1. Turn–On Time

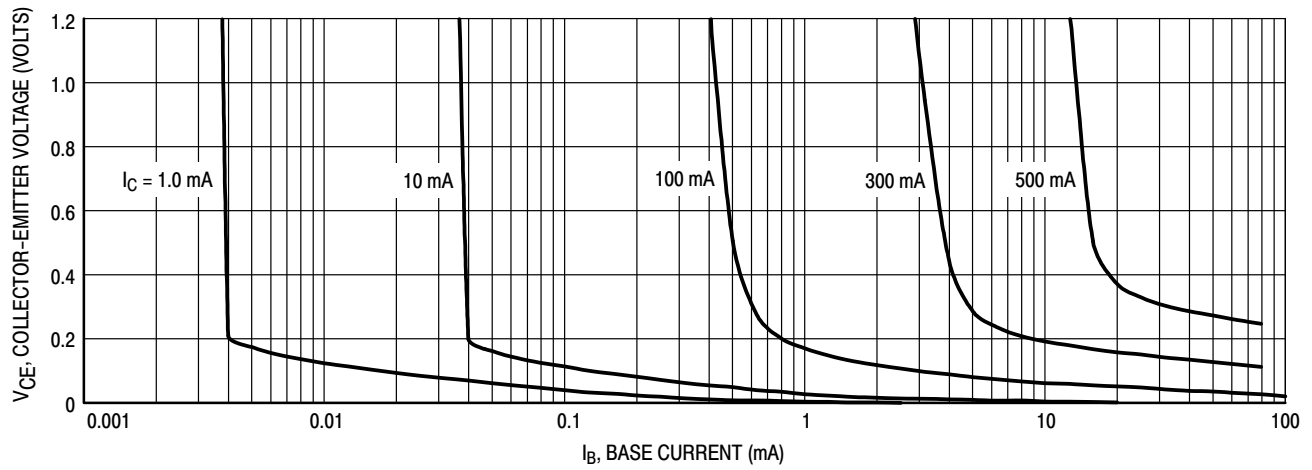Figure 2. Turn–Off Time

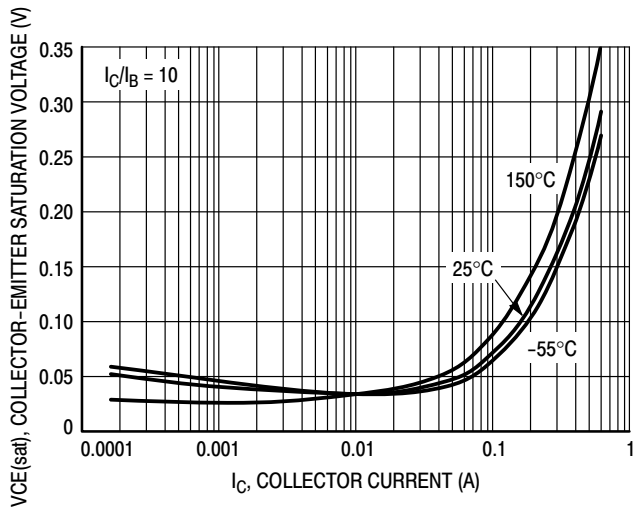**Figure 3. DC Current Gain**

Figure 4. Collector Saturation Region

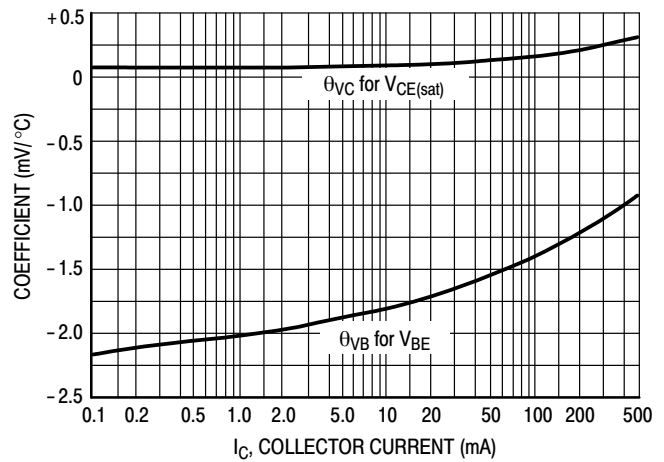**Figure 5. Collector–Emitter Saturation Voltage vs. Collector Current**

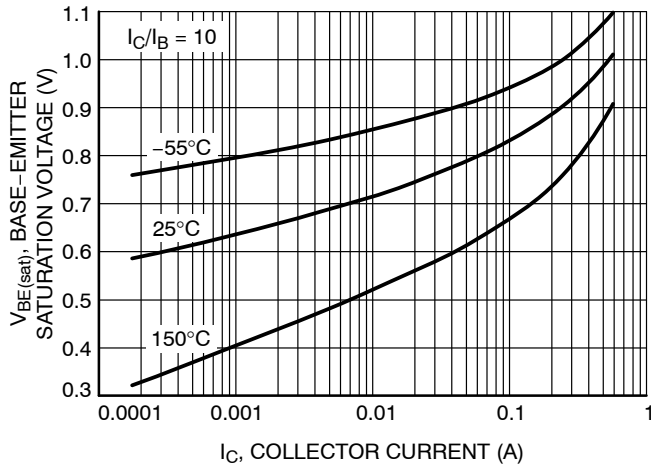**Figure 6. Temperature Coefficients**

Figure 7. Base−Emitter Saturation Voltage vs. Collector Current
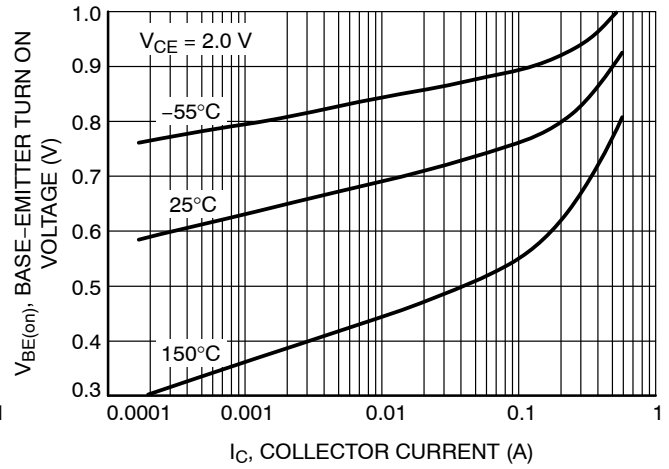

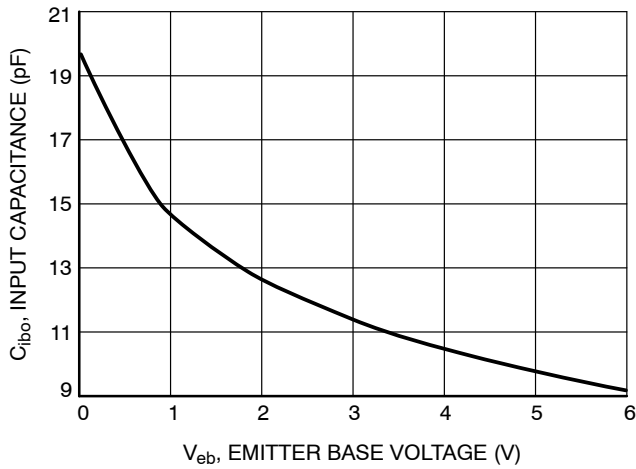**Figure 8. Base−Emitter Turn On Voltage vs. Collector Current**
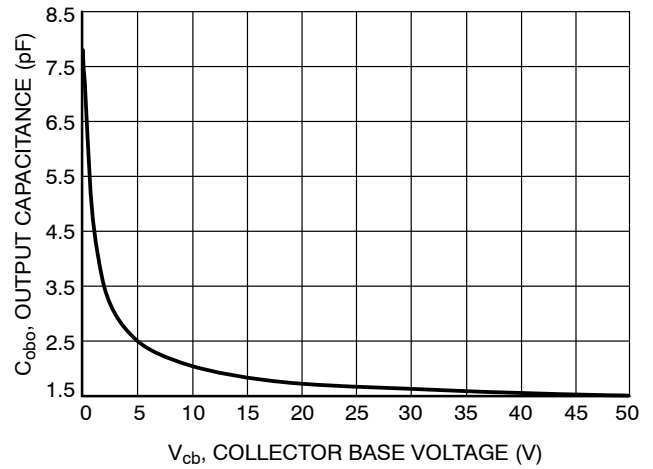

Figure 9. Input Capacitance vs. Emitter Base Voltage
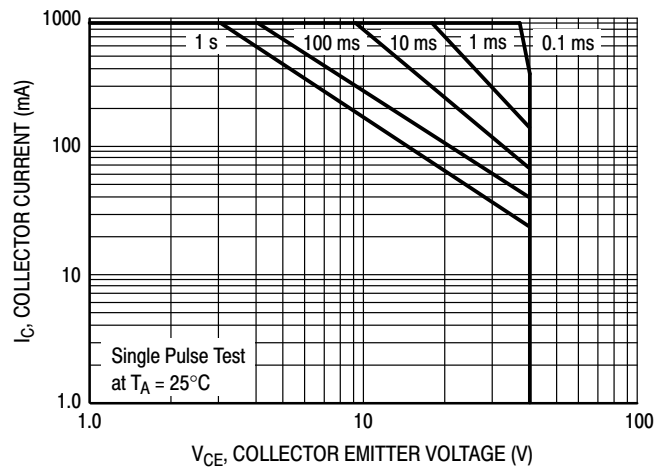

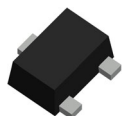**Figure 10. Output Capacitance vs. Collector Base Voltage**

Figure 11. Safe Operating Area

SOT−723 1.20x0.80x0.50, 0.40P
CASE 631AA
ISSUE E

DATE 24 JAN 2024

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
c	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

TOP VIEW

SIDE VIEW

BOTTOM VIEW

RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.
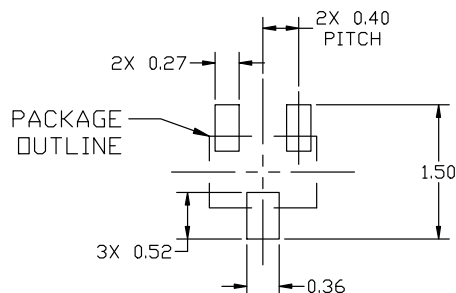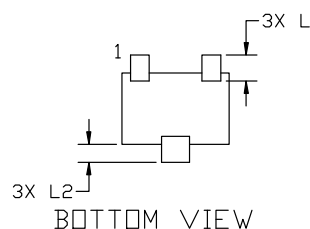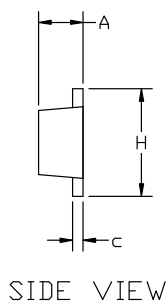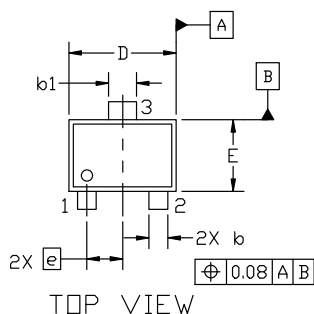
GENERIC MARKING DIAGRAM*

XX M
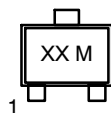
XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
   2. EMITTER
   3. COLLECTOR

STYLE 2:
PIN 1. ANODE
   2. N/C
   3. CATHODE

STYLE 3:
PIN 1. ANODE
   2. ANODE
   3. CATHODE

STYLE 4:
PIN 1. CATHODE
   2. CATHODE
   3. ANODE

STYLE 5:
PIN 1. GATE
   2. SOURCE
   3. DRAIN

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DESCRIPTION:	SOT−723 1.20x0.80x0.50, 0.40P	PAGE 1 OF 1

ADDITIONAL INFORMATION

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